MC74LVX573

Octal D-Type Latch with 3-State Outputs

With 5 V−Tolerant Inputs

The MC74LVX573 is an advanced high speed CMOS octal latch with 3−state outputs. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

This 8−bit D−type latch is controlled by a latch enable input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.
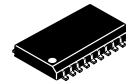
Features

- High Speed: t_{PD} = 6.4 ns (Typ) at V_{CC} = 3.3 V
- Low Power Dissipation: I_{CC} = 4 µA (Max) at T_A = 25°C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: V_{OLP} = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V;
  Machine Model > 200 V
- These Devices are Pb−Free and are RoHS Compliant
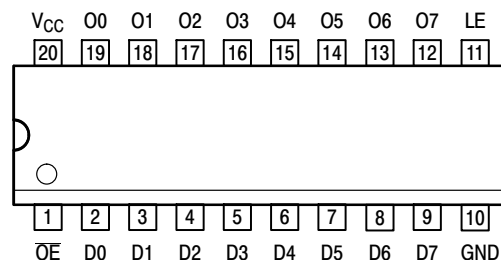
ON Semiconductor®

http://onsemi.com
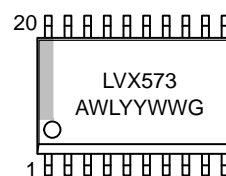
SOIC−20
DW SUFFIX
CASE 751D

TSSOP−20
DT SUFFIX
CASE 948E

PIN ASSIGNMENT

V_{CC}	O0	O1	O2	O3	O4	O5	O6	O7	LE
20	19	18	17	16	15	14	13	12	11
1	2	3	4	5	6	7	8	9	10
$\overline{OE}$	D0	D1	D2	D3	D4	D5	D6	D7	GND

20−Lead (Top View)

MARKING DIAGRAMS

20
LVX573
AWLYYWWG
1

SOIC−20

20
LVX
573
ALYW▪
1
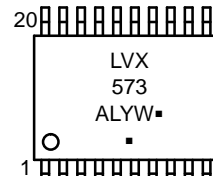
TSSOP−20

LVX573	= Specific Device Code
A	= Assembly Location
WL, L	= Wafer Lot
Y	= Year
WW, W	= Work Week
G or ▪	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.
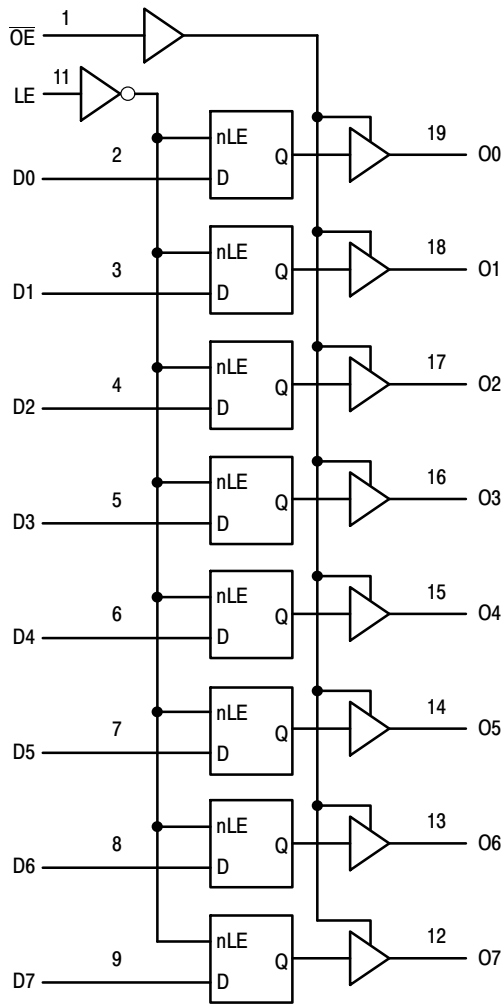
MC74LVX573

Figure 1. Logic Diagram

Table 1. PIN NAMES

Pins	Function
$\overline{OE}$	Output Enable Input
LE	Latch Enable Input
D0–D7	Data Inputs
O0–O7	3–State Latch Outputs

INPUTS			OUTPUTS	
OE	LE	Dn	On	OPERATING MODE
L L	H H	H L	H L	Transparent (Latch Disabled); Read Latch
L L	L L	h l	H L	Latched (Latch Enabled) Read Latch
L	L	X	NC	Hold; Read Latch
H	L	X	Z	Hold; Disabled Outputs
H H	H H	H L	Z Z	Transparent (Latch Disabled); Disabled Outputs
H H	L L	h l	Z Z	Latched (Latch Enabled); Disabled Outputs

H = High Voltage Level; h = High Voltage Level One Setup Time Prior to the Latch Enable High–to–Low Transition; L = Low Voltage Level; l = Low Voltage Level One Setup Time Prior to the Latch Enable High–to–Low Transition; NC = No Change, State Prior to the Latch Enable High–to–Low Transition; X = High or Low Voltage Level or Transitions are Acceptable; Z = High Impedance State; For I_{CC} Reasons DO NOT FLOAT Inputs.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	−0.5 to +7.0	V
V_{in}	DC Input Voltage	−0.5 to +7.0	V
V_{out}	DC Output Voltage	−0.5 to V_{CC} +0.5	V
I_{IK}	Input Diode Current	−20	mA
I_{OK}	Output Diode Current	±20	mA
I_{out}	DC Output Current, per Pin	±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±75	mA
P_D	Power Dissipation	180	mW
T_{stg}	Storage Temperature	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	3.6	V
V_{in}	DC Input Voltage	0	5.5	V
V_{out}	DC Output Voltage	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	−40	+85	°C
$\Delta t/\Delta V$	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} V	$T_A = 25°C$ Min	Typ	Max	$T_A = −40$ to $85°C$ Min	Max	Unit
V_{IH}	High–Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V_{IL}	Low–Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V_{OH}	High–Level Output Voltage ($V_{in} = V_{IH}$ or V_{IL})	$I_{OH} = −50\ \mu A$ $I_{OH} = −50\ \mu A$ $I_{OH} = −4\ mA$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V_{OL}	Low–Level Output Voltage ($V_{in} = V_{IH}$ or V_{IL})	$I_{OL} = 50\ \mu A$ $I_{OL} = 50\ \mu A$ $I_{OL} = 4\ mA$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I_{in}	Input Leakage Current	$V_{in} = 5.5$ V or GND	3.6			±0.1		±1.0	μA
I_{OZ}	Maximum 3–State Leakage Current	$V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	3.6			±0.25		±2.5	μA
I_{CC}	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			4.0		40.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ns)

Symbol	Parameter	Test Conditions		$T_A = 25°C$ Min	Typ	Max	$T_A = −40$ to $85°C$ Min	Max	Unit
t_{PLH}, t_{PHL}	Propagation Delay LE to O	$V_{CC} = 2.7$ V	$C_L = 15$ pF $C_L = 50$ pF		8.2 10.7	15.6 19.1	1.0 1.0	18.5 22.0	ns
		$V_{CC} = 3.3 \pm 0.3$ V	$C_L = 15$ pF $C_L = 50$ pF		6.4 8.9	10.1 13.6	1.0 1.0	12.0 15.5	
t_{PLH}, t_{PHL}	Propagation Delay D to O	$V_{CC} = 2.7$ V	$C_L = 15$ pF $C_L = 50$ pF		7.6 10.1	14.5 18.0	1.0 1.0	17.5 21.0	ns
		$V_{CC} = 3.3 \pm 0.3$ V	$C_L = 15$ pF $C_L = 50$ pF		5.9 8.4	9.3 12.8	1.0 1.0	11.0 14.5	
t_{PZL}, t_{PZH}	Output Enable Time $\overline{OE}$ to O	$V_{CC} = 2.7$ V $R_L = 1$ kΩ	$C_L = 15$ pF $C_L = 50$ pF		7.8 10.3	15.0 18.5	1.0 1.0	18.5 22.0	ns
		$V_{CC} = 3.3 \pm 0.3$ V $R_L = 1$ kΩ	$C_L = 15$ pF $C_L = 50$ pF		6.1 8.6	9.7 13.2	1.0 1.0	12.0 15.5	
t_{PLZ}, t_{PHZ}	Output Disable Time $\overline{OE}$ to O	$V_{CC} = 2.7$ V $R_L = 1$ kΩ	$C_L = 50$ pF		12.1	19.1	1.0	22.0	ns
		$V_{CC} = 3.3 \pm 0.3$ V $R_L = 1$ kΩ	$C_L = 50$ pF		10.1	13.6	1.0	15.5	
t_{OSHL} t_{OSLH}	Output–to–Output Skew (Note 1)	$V_{CC} = 2.7$ V $V_{CC} = 3.3 \pm 0.3$ V	$C_L = 50$ pF $C_L = 50$ pF			1.5 1.5		1.5 1.5	ns

1. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t_{OSHL}) or LOW–to–HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	$T_A = 25°C$			$T_A = -40$ to $85°C$		Unit
		Min	Typ	Max	Min	Max	
C_{in}	Input Capacitance		4	10		10	pF
C_{out}	Maximum 3–State Output Capacitance		6				pF
C_{PD}	Power Dissipation Capacitance (Note 2)		29				pF

2. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/8$ (per latch). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

Symbol	Characteristic	$T_A = 25°C$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.5	0.8	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	−0.5	−0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions	$T_A = 25°C$		$T_A = -40$ to $85°C$	Unit
			Typ	Limit	Limit	
$t_{w(h)}$	Minimum Pulse Width, LE	$V_{CC} = 2.7$ V $V_{CC} = 3.3 \pm 0.3$ V		6.5 5.0	7.5 5.0	ns
t_{su}	Minimum Setup Time, D to LE	$V_{CC} = 2.7$ V $V_{CC} = 3.3 \pm 0.3$ V		5.0 3.5	5.0 3.5	ns
t_h	Minimum Hold Time, D to LE	$V_{CC} = 2.7$ V $V_{CC} = 3.3 \pm 0.3$ V		1.5 1.5	1.5 1.5	ns

MC74LVX573

SWITCHING WAVEFORMS
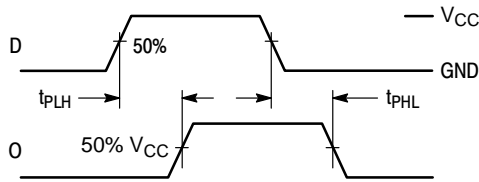
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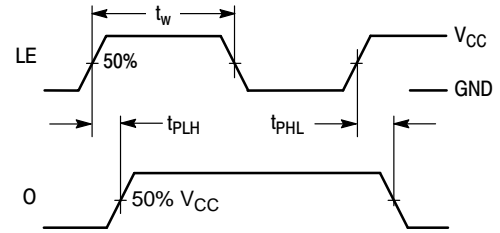
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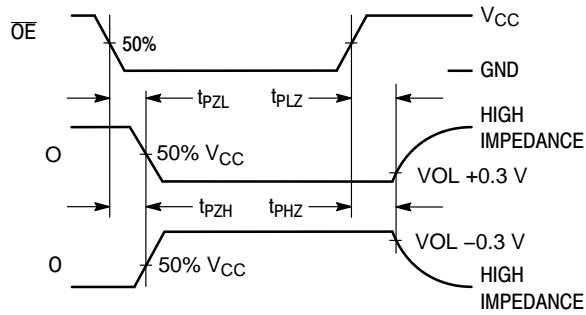
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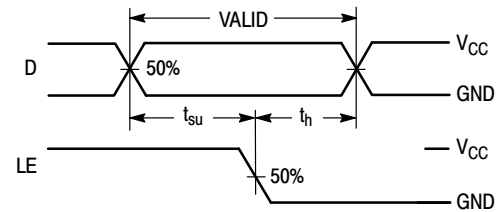
Figure 5.

TEST CIRCUITS
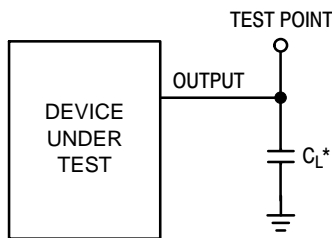
*Includes all probe and jig capacitance

Figure 6. Propagation Delay Test Circuit

CONNECT TO V_{CC} WHEN TESTING t_{PLZ} AND t_{PZL}.
CONNECT TO GND WHEN TESTING t_{PHZ} AND t_{PZH}.
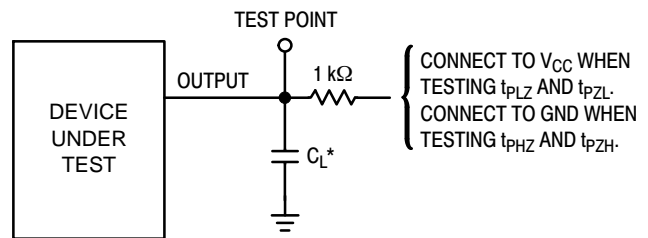
*Includes all probe and jig capacitance

Figure 7. 3–State Test Circuit

ORDERING INFORMATION

Device	Package	Shipping†
MC74LVX573DWR2G	SOIC–20 (Pb–Free)	1000 / Tape & Reel
MC74LVX573DTG	TSSOP–20 (Pb–Free)	75 Units / Rail
MC74LVX573DTR2G	TSSOP–20 (Pb–Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ON Semiconductor®

SOIC−20 WB
CASE 751D−05
ISSUE H

DATE 22 APR 2015

SCALE 1:1
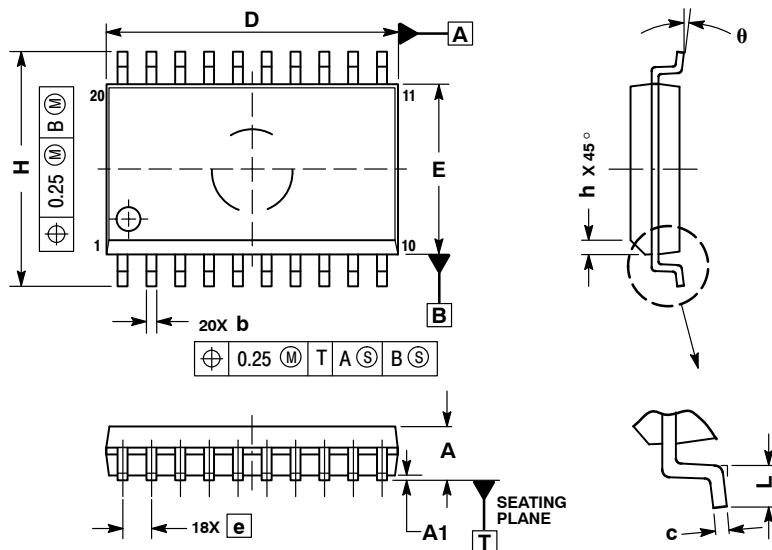
NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0 °	7 °

RECOMMENDED SOLDERING FOOTPRINT*

20X 0.52
20X 1.30
11.00
1.27 PITCH
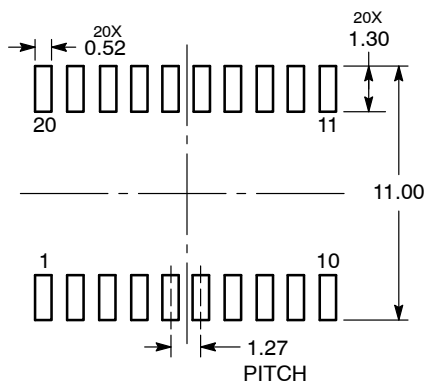
DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

XXXXXXXXXX
XXXXXXXXXX
AWLYYWWG

XXXXX	= Specific Device Code
A	= Assembly Location
WL	= Wafer Lot
YY	= Year
WW	= Work Week
G	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present.

DOCUMENT NUMBER:	98ASB42343B		
DESCRIPTION:	SOIC−20 WB		PAGE 1 OF 1

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®
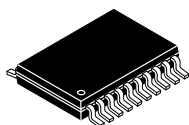
TSSOP−20 WB
CASE 948E
ISSUE D

DATE 17 FEB 2016

SCALE 2:1

20X **K** REF

⊕ |0.15 (0.006)|T|U Ⓢ|

⊕ |0.10 (0.004) Ⓜ|T|U Ⓢ|V Ⓢ|

2X **L/2**

L

PIN 1
IDENT

B

−U−

⊕ |0.15 (0.006)|T|U Ⓢ|

A

−V−

K

K1

J **J1**

SECTION N−N

0.25 (0.010)

N

M

N

F

DETAIL E

C

D **G** **H**

⌒ |0.100 (0.004)|

−T− SEATING
PLANE

−W−

DETAIL E
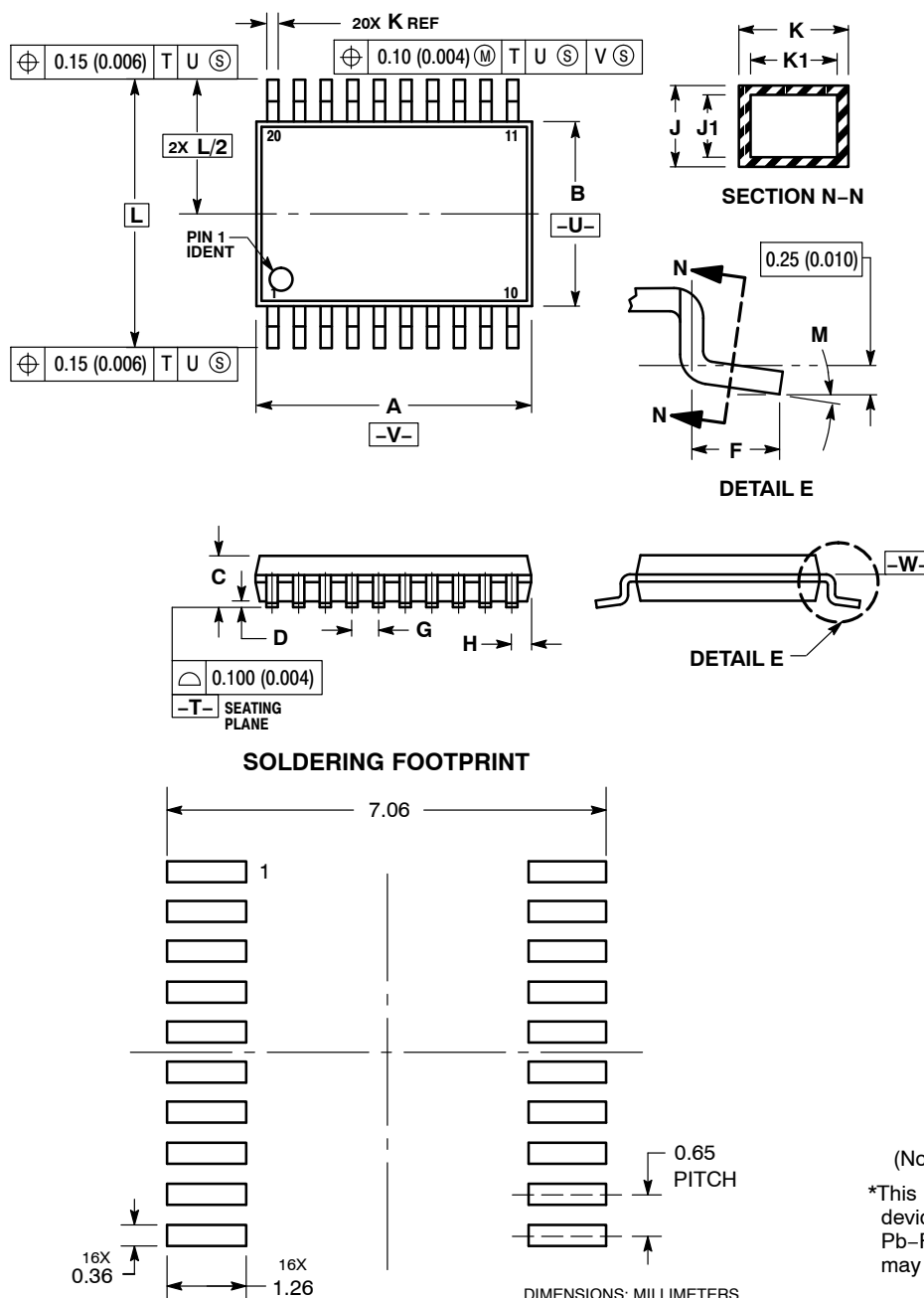
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT

7.06

1

0.65
PITCH

16X
0.36

16X
1.26

DIMENSIONS: MILLIMETERS

GENERIC
MARKING DIAGRAM*

XXXX
XXXX
ALYW▪
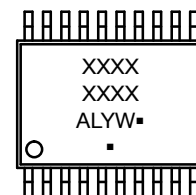
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98ASH70169A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TSSOP−20 WB		PAGE 1 OF 1

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PUBLICATION ORDERING INFORMATION

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